

CIR-S3SUHI1002G

DDR3 SO-DIMM 1066MHz 2GB

Description

The CIR-S3SUHI1002G is 256M words X 64 bits, 1 rank. Unbuffered Small Outline dual in line memory module (SO-DIMM). DDR3 SDRAMs in Fine Ball Grid Array (FBGA) packages on a 204pin glass-epoxy substrate. Provide a high performance 8 byte interface in 67.60mm width form factor of industry standard. It is suitable for easy interchange and addition.

Specifications

Density	2GB
Pin Count	204pin
Type	Unbuffered
Dimensions	67.6mm x 30.0mm
ECC	Non-ECC
Component Config	256M x 8 bit
Data Rate	1066 Mbps
CAS Latency	7
Voltage:	1.5V / 1.35V
PCB Layers	8
Operating Temp.(TCASE)	0°C~+85°C
Module Ranks	Single Rank

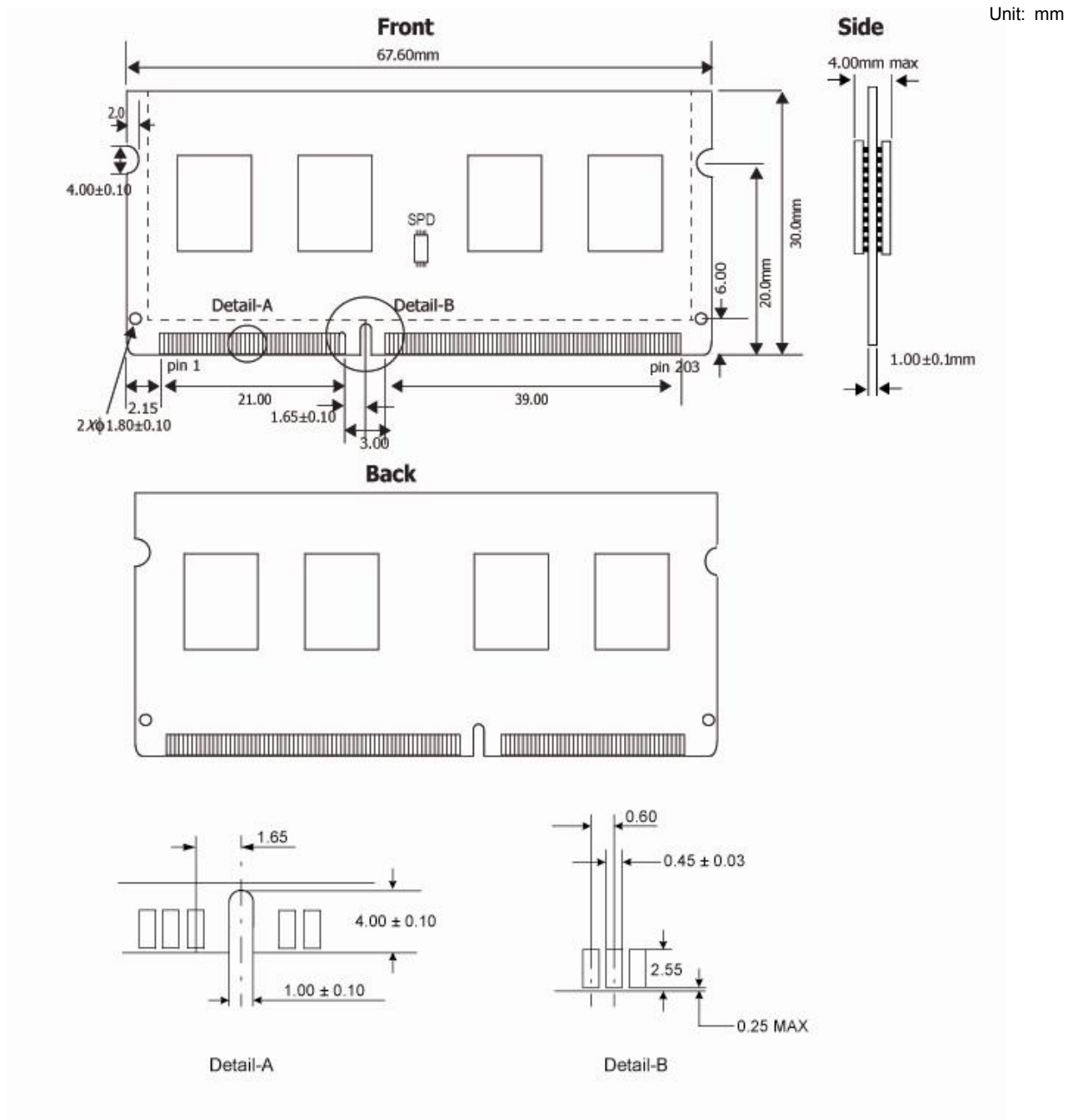
Features

- Data rate: 1066Mbps
- RoHS compliant products.
- 204pin, Small outline dual in line memory module (SO-DIMM)
- Power supply: VDD= 1.5V (1.425V to 1.575V) & VDD= 1.35V (1.283V to 1.45V)
- Interface: SSTL_15
- Programmable CAS Latency (CL): 6, 7, 8 support
- Fully differential clock inputs (CK, /CK) operation
- Differential Data Strobe (DQS, /DQS)
- Serial presence detect with EEPROM
- 8 independent internal bank
- 8K refresh cycles / 64ms
- On-Die-Termination (ODT) for better signal quality
- Asynchronous RESET pin supported
- ZQ calibration supported
- POSTED CAS additive latency (AL)
- Bi-directional Differential Data Strobe
- Burst Length: 4, 8
- 8 bit pre-fetch
- TCASE of 0°C to 95°C (Components)
 - 64ms, 8,192 cycle refresh at 0°C to 85°C
 - 32ms at 85°C to 95°C

Speed Grade

Frequency Grade	Data Transfer Rate	CAS Latency Support			CL-tRCD-tRP
		CL6	CL7	CL8	
DDR3-1066	PC3-8500	800	1066	1066	7-7-7

Package Dimensions



Tolerances : ± 0.15mm unless otherwise specified